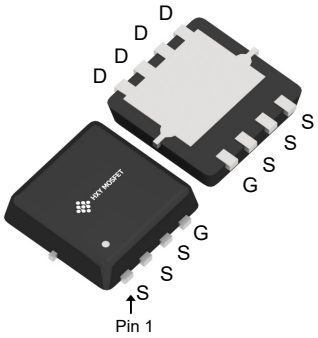
# NVTFS5C658NLTAG

N-SGT Enhancement Mode MOSFET

## Description

The NVTFS5C658NLTAG use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.This device is specially designed to get better ruggedness and suitable.

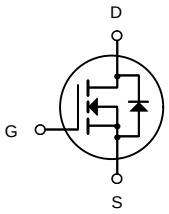



DFN3X3-8L

## General Features

$V_{DS}$ =60V $I_D$ =100A

$R_{DS(ON)}$ < 4.8mΩ@ $V_{GS}$=10V




N-Channel MOSFET

## Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

## Package Marking and Ordering Information

| Product ID | Pack | Brand | Qty(PCS) |
|---|---|---|---|
| NVTFS5C658NLTAG | DFN3X3-8L | HXY MOSFET | 5000 |

## Absolute Maximum Ratings at $T_j$=25°C unless otherwise noted

| Parameter | | Symbol | Value | Unit |
|---|---|---|---|---|
| Drain source voltage | | $V_{DS}$ | 60 | V |
| Gate source voltage | | $V_{GS}$ | ±20 | V |
| Continuous drain current | $T_C$=25°C | $I_D$ | 100 | A |
| Continuous drain current | $T_C$=100°C | $I_D$ | 64 | A |
| Pulsed drain current[1] | | $I_{DM}$ | 385 | A |
| Power dissipation | | $P_D$ | 73.5 | W |
| Single pulsed avalanche energy[2] | | EAS | 80 | mJ |
| Operation and storage temperature | | Tstg,Tj | -55 to 150 | ℃ |
| Thermal resistance, junction-case | | $R_{\theta JC}$ | 1.7 | °C/W |
| Thermal resistance, junction-ambient[4)] | | $R_{\theta JA}$ | 51 | °C/W |

## Electrical Characteristics ($T_J$=25°C, unless otherwise noted)

| Parameter | | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|---|
| Drain-Source Breakdown Voltage | | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ = 250μA | 60 | - | - | V |
| Gate-body Leakage Current | | $I_{GSS}$ | $V_{DS}$ = 0V, $V_{GS}$ = ±20V | - | - | ±100 | nA |
| Zero Gate Voltage Drain Current | $T_J$=25°C | $I_{DSS}$ | $V_{DS}$ = 60V, $V_{GS}$ = 0V | - | - | 1 | μA |
| | $T_J$=100°C | | | - | - | | |
| Gate-Threshold Voltage | | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | 1.2 | 1.7 | 2.5 | V |
| Drain-Source On-Resistance[4] | | $R_{DS(on)}$ | $V_{GS}$ = 10V, $I_D$ = 21A | - | 4.0 | 4.8 | mΩ |
| | | | $V_{GS}$ = 4.5V, $I_D$ = 10A | - | 5.2 | 6.6 | |
| Forward Transconductance[4] | | $g_{fs}$ | $V_{DS}$ = 10V, $I_D$ = 21A | - | 89 | - | S |
| Input Capacitance | | $C_{iss}$ | $V_{DS}$ = 30V, $V_{GS}$ =0V, f =1MHz | - | 2180 | - | pF |
| Output Capacitance | | $C_{oss}$ | | - | 735 | - | |
| Reverse Transfer Capacitance | | $C_{rss}$ | | - | 42 | - | |
| Gate Resistance | | $R_g$ | f = 1MHz | - | 1.8 | - | Ω |
| Total Gate Charge | | $Q_g$ | $V_{GS}$ = 10V, $V_{DS}$ = 30V, $I_D$= 21A | - | 35 | - | nC |
| Gate-Source Charge | | $Q_{gs}$ | | - | 6.6 | - | |
| Gate-Drain Charge | | $Q_{gd}$ | | - | 8.4 | - | |
| Turn-On Delay Time | | $t_{d(on)}$ | $V_{GS}$ =10V, $V_{DD}$ = 30V, $R_G$ = 3Ω, $I_D$= 21A | - | 9.4 | - | ns |
| Rise Time | | $t_r$ | | - | 8.4 | - | |
| Turn-Off Delay Time | | $t_{d(off)}$ | | - | 32.5 | - | |
| Fall Time | | $t_f$ | | - | 12.5 | - | |
| Body Diode Reverse Recovery Time | | $t_{rr}$ | $I_F$=20A, dI/dt=100A/μs | - | 50 | - | ns |
| Body Diode Reverse Recovery Charge | | $Q_{rr}$ | | - | 20 | - | nC |
| Diode Forward Voltage[4] | | $V_{SD}$ | $I_S$ = 21A, $V_{GS}$ = 0V | - | - | 1.2 | V |
| Continuous Source Current | $T_C$=25°C | $I_S$ | - | - | - | 100 | A |

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C
2. The EAS data shows Max. rating . The test condition is $V_{DD}$=25V,$V_{GS}$=10V,L=0.1mH，$I_{AS}$=40A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

## Typical Characteristics

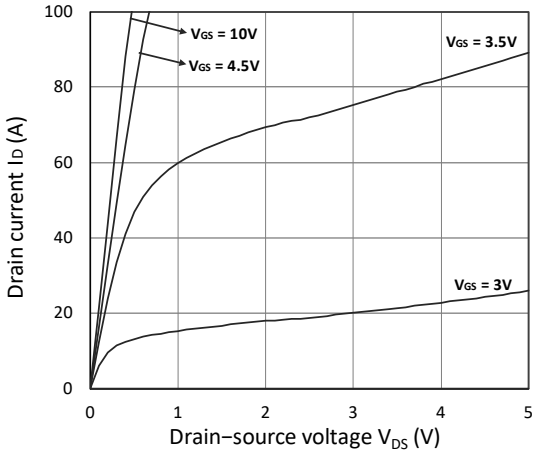



Figure 1. Output Characteristics

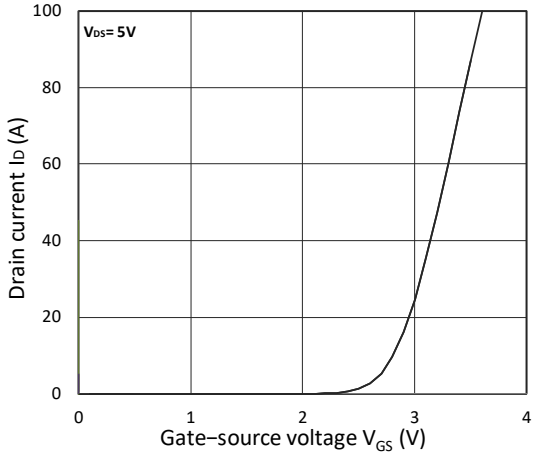



Figure 2. Transfer Characteristics

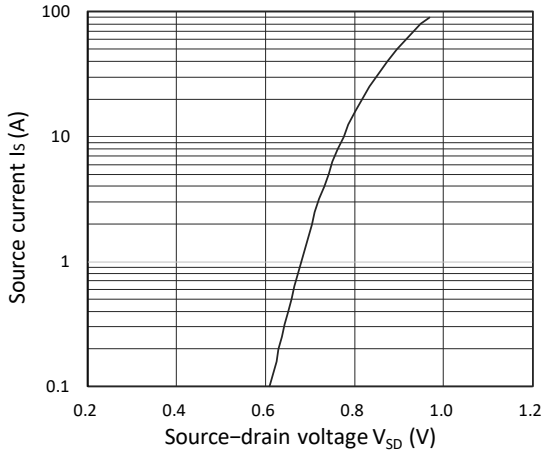



Figure 3. Forward Characteristics of Reverse

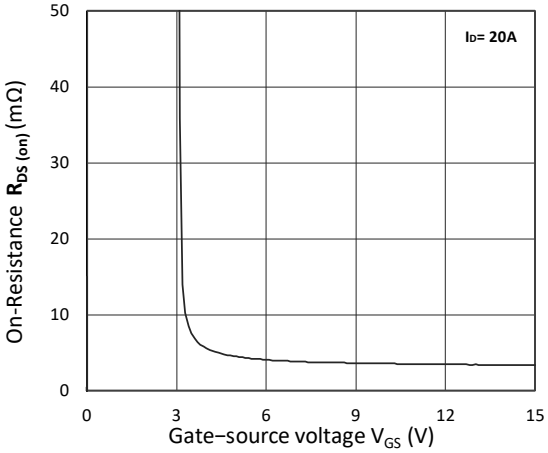



Figure 4. $R_{DS(ON)}$ vs. $V_{GS}$

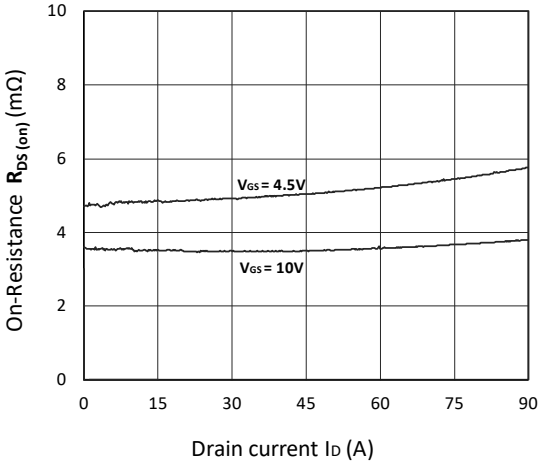



Figure 5. $R_{DS(ON)}$ vs. $I_D$

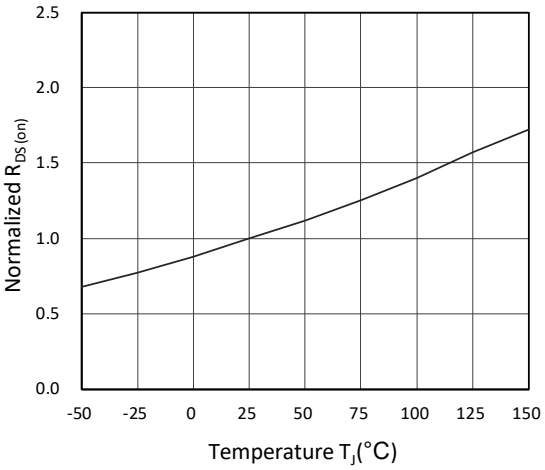



Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

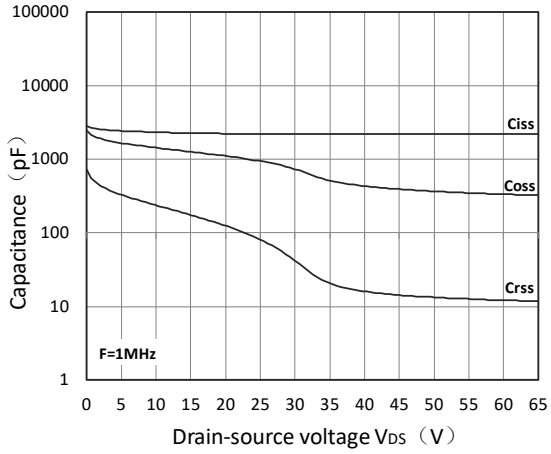



Figure 7. Capacitance Characteristics

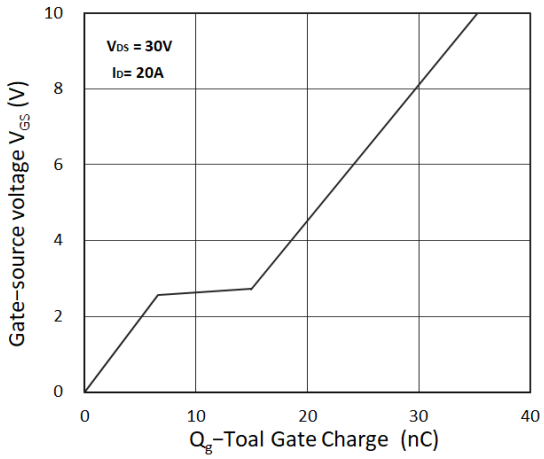



Figure 8. Gate Charge Characteristics

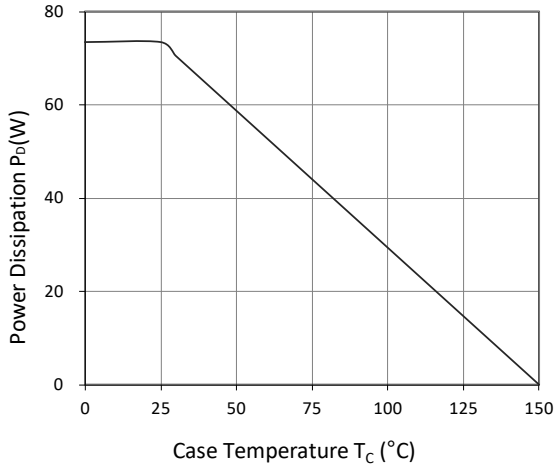



Figure 9. Power Dissipation

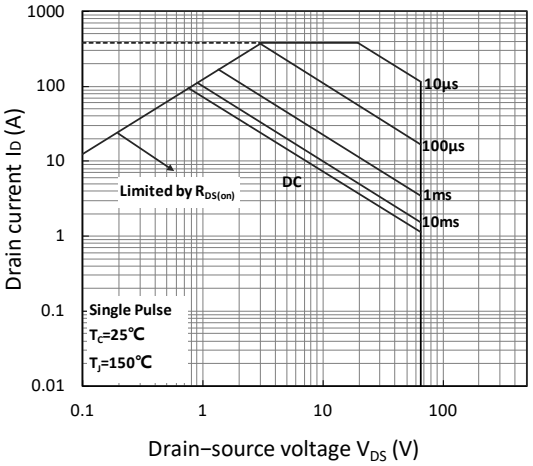



Figure10. Safe Operating Area

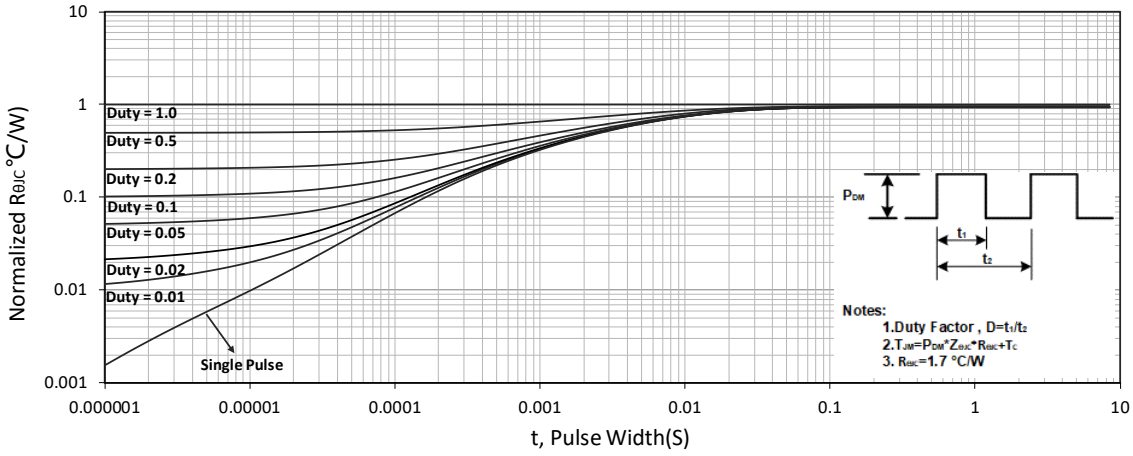



Figure 11. Normalized Maximum Transient Thermal Impedance

## Test Circuit

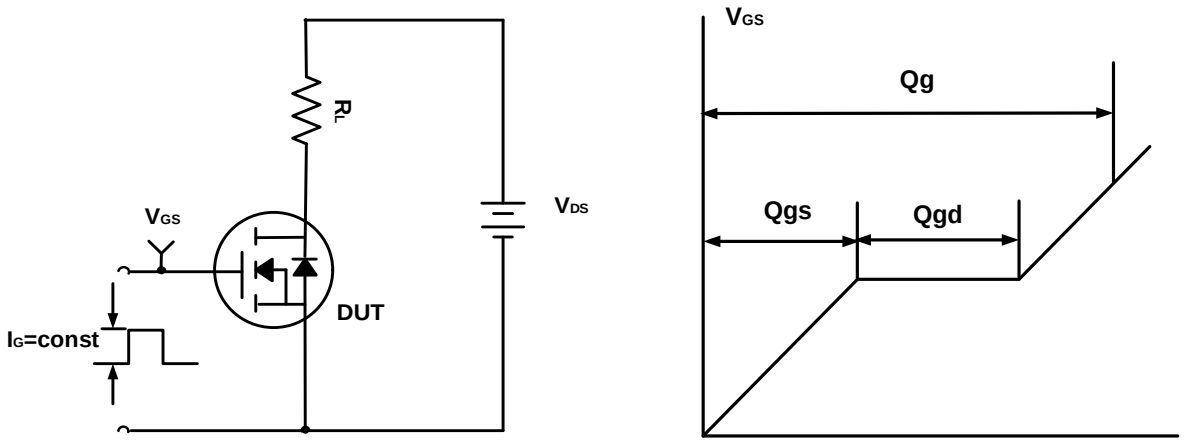



**Figure A. Gate Charge Test Circuit & Waveforms**

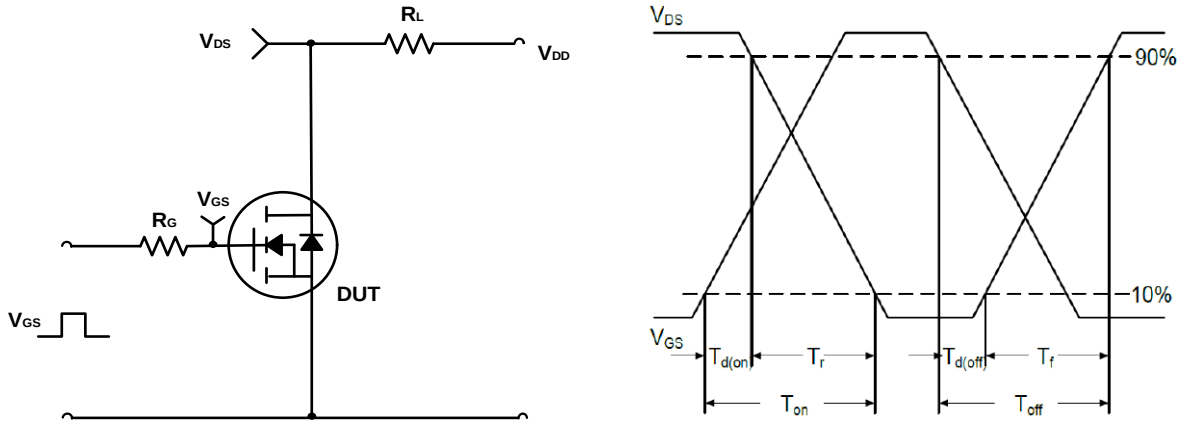



**Figure B. Switching Test Circuit & Waveforms**

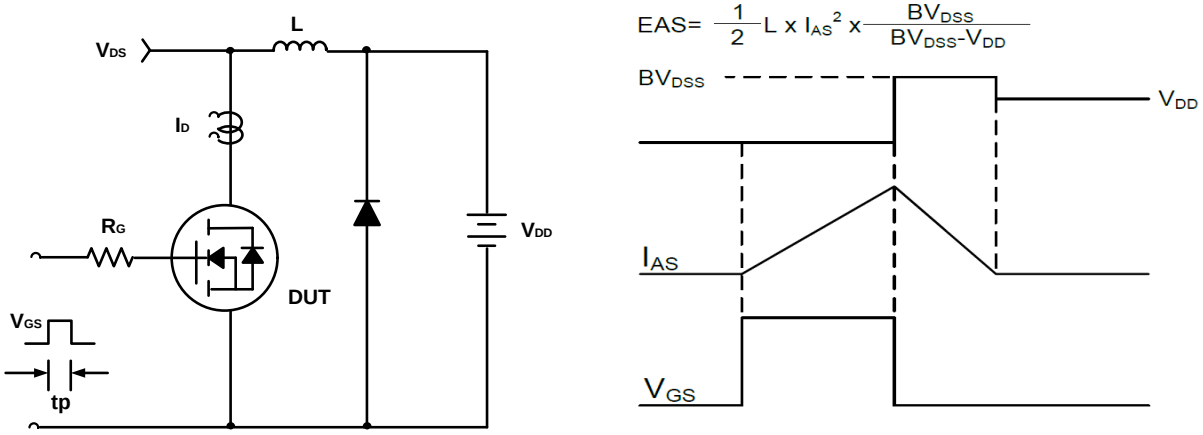
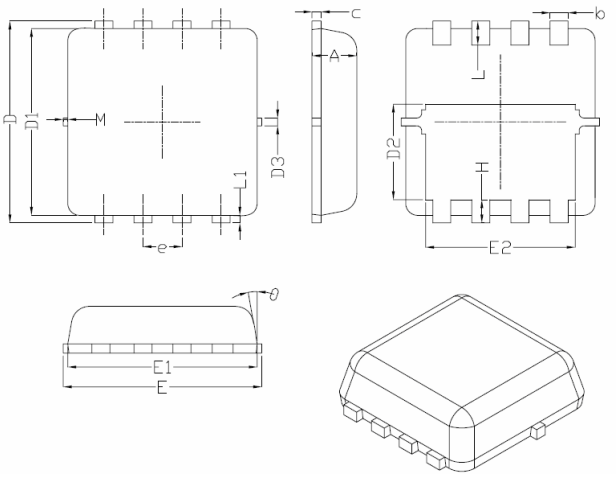



**Figure C. Unclamped Inductive Switching Circuit & Waveforms**

## DFN3X3-8L Package Information




| Symbol | Dimensions In Millimeters | | |
|---|---|---|---|
| | Min. | Nom. | Max. |
| A | 0.70 | 0.75 | 0.80 |
| b | 0.25 | 0.30 | 0.35 |
| c | 0.10 | 0.15 | 0.25 |
| D | 3.25 | 3.35 | 3.45 |
| D1 | 3.00 | 3.10 | 3.20 |
| D2 | 1.48 | 1.58 | 1.68 |
| D3 | - | 0.13 | - |
| E | 3.20 | 3.30 | 3.40 |
| E1 | 3.00 | 3.15 | 3.20 |
| E2 | 2.39 | 2.49 | 2.59 |
| e | 0.65BSC | | |
| H | 0.30 | 0.39 | 0.50 |
| L | 0.30 | 0.40 | 0.50 |
| L1 | - | 0.13 | - |
| M | * | * | 0.15 |
| θ | | 10° | 12° |

## Attention

■ Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

■ Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer’s products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer’s products or equipment.

■ HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could
give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

# Unikeyic Electronics

Global Electronic Components Distributor

Click to view pricing, inventory, delivery, and lifecycle information:

## HXY MOSFET:

BZT52C3V3S HXY2101EI MAX487ESA P6SMB33CA HXY2300MI HC4D20120A HESDNC5VB1AF-B HT7150 IRLML6246PBF HMCP602-I/SN SQJA04EP-T1_BE3 BZT52C13 HAD8542ARZ SD15C SS1045 PESD5V0S1BB TPSMB100CA-VR DTC143ZE HT7540-1 P6SMB200A SS510C HOPA2340UA HXY8205ES MMBT3904T P6SMB36CA TPSMB28A-VR US2M HC3D10170A SS10100 SS5150B